Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Supplementary Information:

Ultrafast Charge Carrier Relaxation and Charge Transfer Processes in CdS/CdTe Thin Films

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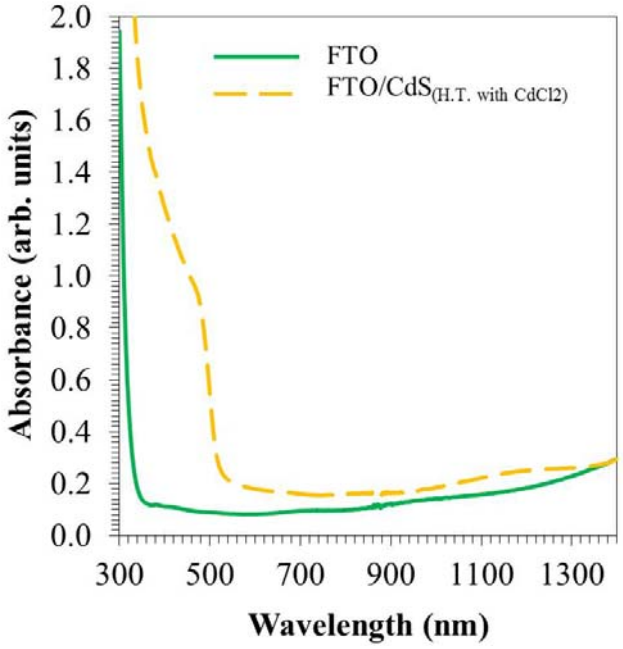

Figure S.1: UV/visible/near-IR absorption spectra of the substrate (FTO) and CdS thin films.

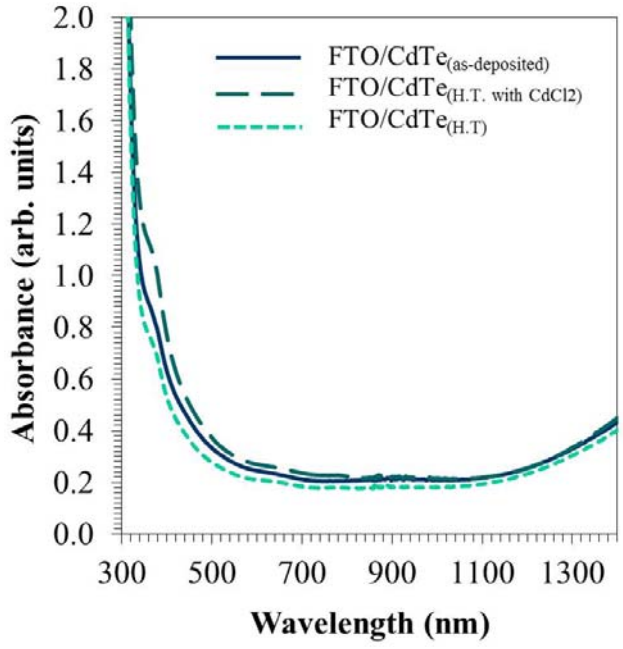

Figure S.2: UV/visible/near-IR absorption spectra of CdTe thin films.

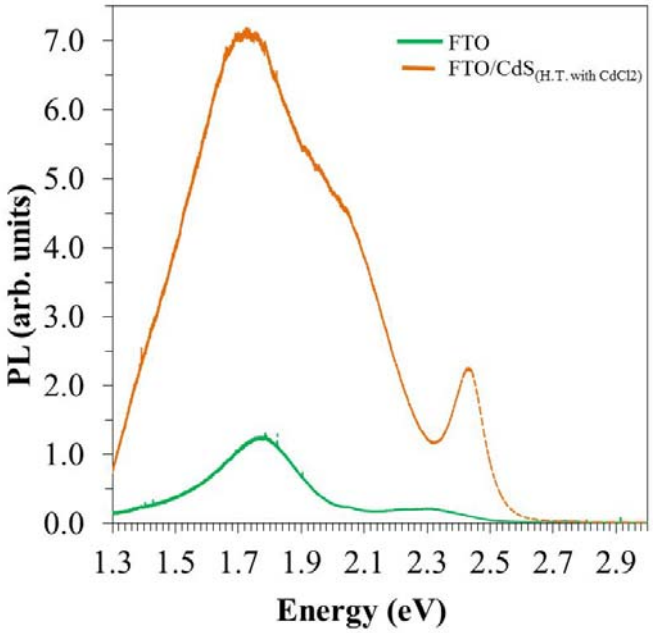

Figure S.3: Photoluminescence spectra of the substrate (FTO) and CdS thin films with 442 nm (2.81 eV) excitation.

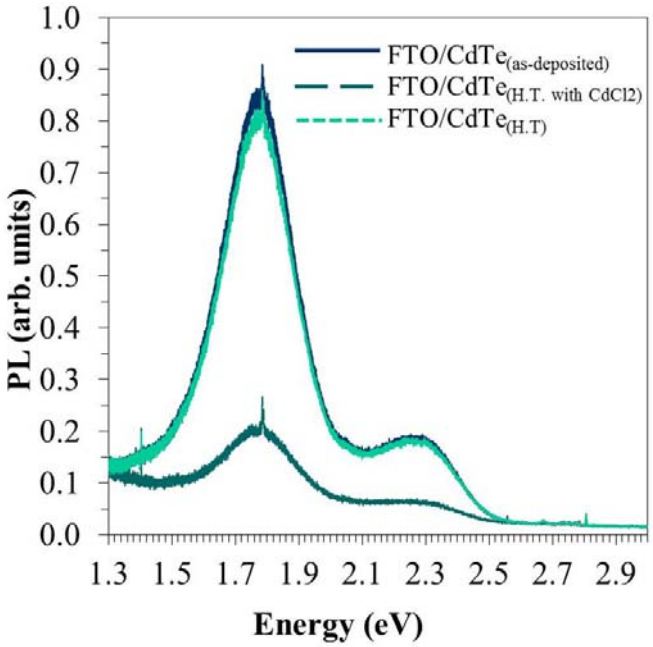

Figure S.4: Photoluminescence spectra of CdTe thin films with 442 nm (2.81 eV) excitation.

Table S.1: Time constants (τ_1 and τ_2) and weights (A_1 and A_2) derived in fitting the PB recovery kinetics of the CdS thin film (Fig. 4b).

λ_{probe} (nm)	τ_1 (ps)	A_1 (%)	τ_2 (ps)	A_2 (%)
455	1.15±0.07	21	384±9	79
475	0.90±0.12	23	414±8	77
530	0.68±0.09	58	413±10	42